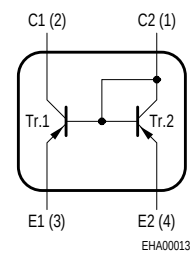
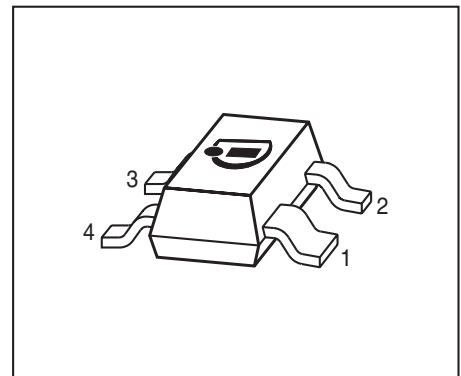


PNP Silicon Double Transistor

- To be used as a current mirror
- Good thermal coupling and V_{BE} matching
- High current gain
- Low collector-emitter saturation voltage
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Type	Marking	Pin Configuration				Package
BCV62A	3Js	1 = C2	2 = C1	3 = E1	4 = E2	SOT143
BCV62B	3Ks	1 = C2	2 = C1	3 = E1	4 = E2	SOT143
BCV62C	3Ls	1 = C2	2 = C1	3 = E1	4 = E2	SOT143

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage (transistor T1)	V_{CEO}	30	V
Collector-base voltage (open emitter) (transistor T1)	V_{CBO}	30	
Emitter-base voltage	V_{EBS}	6	
DC collector current	I_C	100	mA
Peak collector current	I_{CM}	200	
Base peak current (transistor T1)	I_{BM}	200	
Total power dissipation, $T_S = 99\text{ °C}$	P_{tot}	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤170	K/W
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¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

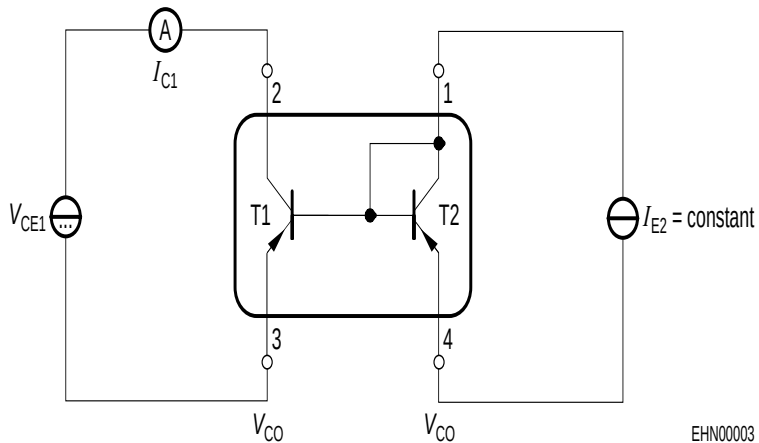
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics of T1					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	30	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	30	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector cutoff current $V_{CB} = 30\text{ V}, I_E = 0$	I_{CBO}	-	-	15	nA
Collector cutoff current $V_{CB} = 30\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	-	-	5	μA
DC current gain 1) $I_C = 0.1\text{ mA}, V_{CE} = 5\text{ V}$	h_{FE}	100	-	-	-
DC current gain 1) $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}$	h_{FE}				
BCV62A		125	180	220	
BCV62B		220	290	475	
BCV62C	420	520	800		
Collector-emitter saturation voltage1) $I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}, I_B = 5\text{ mA}$	V_{CEsat}	- -	75 250	300 650	mV
Base-emitter saturation voltage 1) $I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}, I_B = 5\text{ mA}$	V_{BEsat}	- -	700 850	- -	
Base-emitter voltage 1) $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	600 -	650 -	750 820	

1) Pulse test: $t \leq 300\mu\text{s}$, $D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

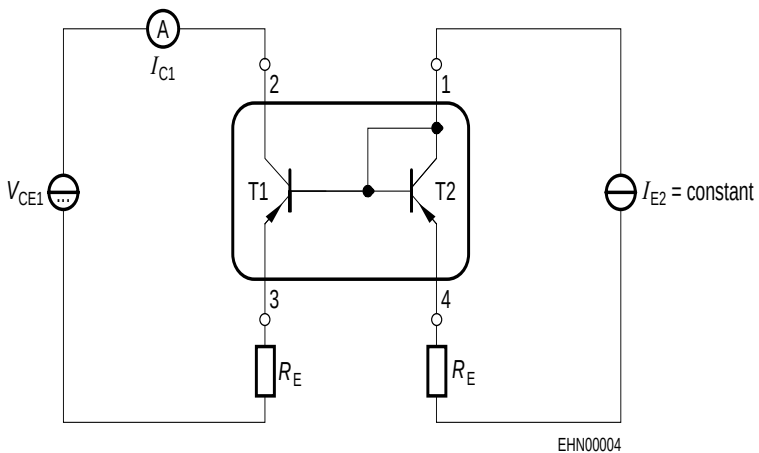
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Base-emitter forward voltage $I_E = 10\ \mu\text{A}$ $I_E = 250\ \text{mA}$	V_{BES}	0.4 -	- -	- 1.8	V
Matching of transistor T1 and transistor T2 at $I_{\text{E}2} = 0.5\text{mA}$ and $V_{\text{CE}1} = 5\text{V}$ $T_A = 25\ ^\circ\text{C}$ $T_A = 150\ ^\circ\text{C}$	$I_{\text{C}1} / I_{\text{C}2}$	- 0.7 0.7	- - -	- 1.3 1.3	-
Thermal coupling of transistor T1 and transistor T2 1) T1: $V_{\text{CE}} = 5\text{V}$ Maximum current of thermal stability of $I_{\text{C}1}$	$I_{\text{E}2}$	-	5	-	mA
AC characteristics of transistor T1					
Transition frequency $I_{\text{C}} = 10\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$, $f = 100\ \text{MHz}$	f_{T}	-	250	-	MHz
Collector-base capacitance $V_{\text{CB}} = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_{cb}	-	1.5	-	pF
Emitter-base capacitance $V_{\text{EB}} = 0.5\ \text{V}$, $f = 1\ \text{MHz}$	C_{eb}	-	8	-	
Noise figure $I_{\text{C}} = 200\ \mu\text{A}$, $V_{\text{CE}} = 5\ \text{V}$, $R_{\text{S}} = 2\ \text{k}\Omega$, $f = 1\ \text{kHz}$, $\Delta f = 200\ \text{Hz}$	F	-	2	-	dB
Short-circuit input impedance $I_{\text{C}} = 1\ \text{mA}$, $V_{\text{CE}} = 10\ \text{V}$, $f = 1\ \text{kHz}$	$h_{11\text{e}}$	-	4.5	-	kΩ
Open-circuit reverse voltage transf.ratio $I_{\text{C}} = 1\ \text{mA}$, $V_{\text{CE}} = 10\ \text{V}$, $f = 1\ \text{kHz}$	$h_{12\text{e}}$	-	2	-	10 ⁻⁴
Short-circuit forward current transf.ratio $I_{\text{C}} = 1\ \text{mA}$, $V_{\text{CE}} = 10\ \text{V}$, $f = 1\ \text{kHz}$	$h_{21\text{e}}$	100	-	900	-
Open-circuit output admittance $I_{\text{C}} = 1\ \text{mA}$, $V_{\text{CE}} = 10\ \text{V}$, $f = 1\ \text{kHz}$	$h_{22\text{e}}$	-	30	-	μS

1) Witout emitter resistor. Device mounted on alumina 15mm x 16.5mm x 0.7mm

Test circuit for current matching


EHN00003

Note: Voltage drop at contacts: $V_{CO} < 2/3 V_T = 16\text{mV}$

Characteristic for determination of V_{CE1} at specified R_E range with I_{E2} as parameter under condition of $I_{C1}/I_{E2} = 1.3$


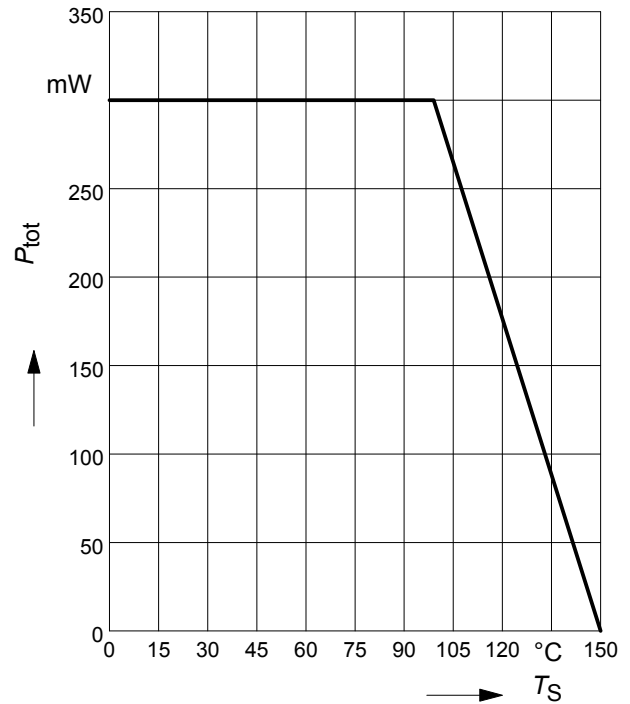
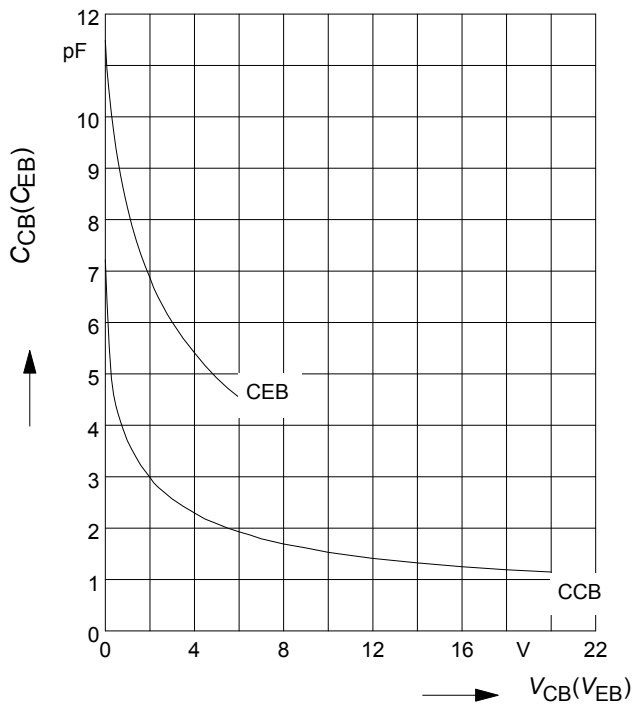
EHN00004

Note: BCV62 with emitter resistors

Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$

Total power dissipation $P_{tot} = f(T_S)$



Permissible pulse load

$P_{totmax} / P_{totDC} = f(t_p)$

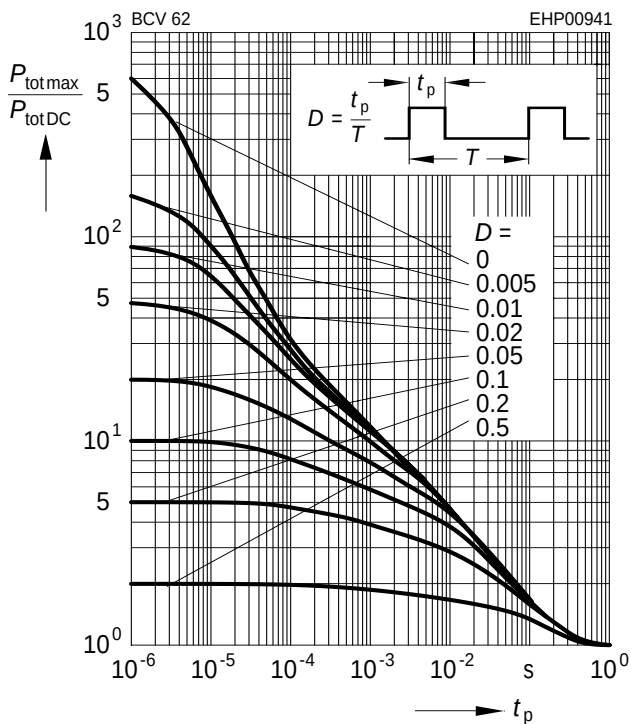


Diagram illustrating the marking on the BFP181 package:

- Manufacturer:** infineon
- Date code (YM):** 2005, June
- Pin 1:** Indicated by an arrow pointing to the first pin on the left.
- Type code:** BFP181

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